



V

nC

-20

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SLPS221A-OCTOBER 2009-REVISED OCTOBER 2010

Dual P-Channel NexFET™ Power MOSFET

Check for Samples: CSD75204W15

V_{D1D2}

Qg

FEATURES

- **Dual P-Ch MOSFETs**
- **Common Source Configuration**
- Small Footprint 1.5-mm × 1.5-mm
- Gate-Source Voltage Clamp
- Gate ESD Protection -3kV
- Pb Free
- **RoHS Compliant**
- **Halogen Free**

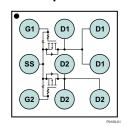
APPLICATIONS

- **Battery Management**
- **Battery Protection**

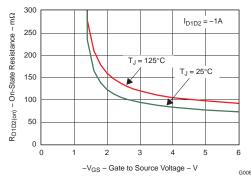
DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile. Low on resistance coupled with the small footprint and low profile make the device ideal for battery operated space constrained applications.

Top View







Gate Charge Total (-4.5V)

Drain to Drain Voltage

Q _{gd}	Gate Charge Gate to Drain	0.6		nC
R _{D1D2(on)}	Drain to Drain On Resistance	$V_{GS} = -1.8V$	140	mΩ
		$V_{GS} = -2.5V$	105	mΩ
		$V_{GS} = -4.5V$	80	mΩ
V _{GS(th)}	Threshold Voltage	-0.7		V

PRODUCT SUMMARY

ORDERING INFORMATION

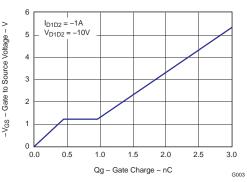
Device	Package	Media	Qty	Ship
CSD75204W15	1.5-mm × 1.5-mm Wafer Level Package	7-Inch Reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 28$	5°C unless otherwise stated	VALUE	UNIT
V_{D1D2}	Drain to Drain Voltage	-20	V
V_{GS}	Gate to Source Voltage	-6	V
	Continuous Drain to Drain Current, $T_C = 25^{\circ}C^{(1)}$	-3	А
I _{D1D2}	Pulsed Drain to Drain Current, T _C = $25^{\circ}C^{(2)}$	-28	А
	Continuous Source Pin Current	-1.2	А
I _S	Pulsed Source Pin Current ⁽²⁾	-15	А
	Continuous Gate Clamp Current	-0.5	А
I _G	Pulsed Gate Clamp Current ⁽²⁾	-7	А
PD	Power Dissipation ⁽¹⁾	0.7	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

(1) Per device, both sides in conduction

(2) Pulse duration 10µs, duty cycle ≤2%



Gate Charge (Per MOSFET)

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated). Specifications and graphs are Per MOSFET unless otherwise stated. Drain to Drain measurements are done with both MOSFETs in series (common source configuration.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Ch	aracteristics					
BV _{D1D2}	Drain to Drain Voltage	$V_{GS} = 0V, I_{D1D2} = -250\mu A$	-20			V
BV _{GSS}	Gate to Source Voltage	V _{D1D2} = 0V, I _G = -250μA	-6.1		-7.2	V
I _{DDS}	Drain to Drain Leakage Current	$V_{GS} = 0V, V_{D1D2} = -16V$			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{D1D2} = 0V, V_{GS} = -6V$			-100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{D1D2} = V_{GS}, I_{DS} = -250 \mu A$	-0.5	-0.7	-0.9	V
		$V_{GS} = -1.8V, I_{D1D2} = -1A$		140	175	mΩ
R _{D1D2(on)}	Drain to Drain On Resistance	$V_{GS} = -2.5V, I_{D1D2} = -1A$		105	130	mΩ
		$V_{GS} = -4.5V, I_{D1D2} = -1A$		80	100	mΩ
9 _{fs}	Transconductance	$V_{D1D2} = -10V, I_{D1D2} = -1A$		5.3		S
Dynamic	Characteristics					
C _{ISS}	Input Capacitance			315	410	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{D1D2} = -10V,$ f = 1MHz		128	165	pF
C _{RSS}	Reverse Transfer Capacitance			43	55	pF
Qg	Gate Charge Total (-4.5V)			2.8	3.9	nC
Q _{gd}	Gate Charge - Gate to Drain	$V_{D1D2} = -10V$,		0.6		nC
Q _{gs}	Gate Charge - Gate to Source	$I_{D1D2} = -1A$		0.5		nC
Q _{g(th)}	Gate Charge at Vth			0.2		nC
Q _{OSS}	Output Charge	$V_{D1D2} = -9.5V, V_{GS} = 0V$		2.2		nC
t _{d(on)}	Turn On Delay Time			7.8		ns
t _r	Rise Time	$V_{D1D2} = -10V, V_{GS} = -4.5V,$		6.7		ns
t _{d(off)}	Turn Off Delay Time	$I_{D1D2} = -1A, R_G = 30\Omega$		45		ns
t _f	Fall Time			26		ns
Diode Ch	aracteristics				ŀ	
V _{SD}	Diode Forward Voltage	$I_{D1D2} = -1A, V_{GS} = 0V$		0.75	1	V
Q _{rr}	Reverse Recovery Charge	$V_{dd} = -9.5V$, $I_F = -1A$, $di/dt = 200A/\mu s$		10.5		nC
t _{rr}	Reverse Recovery Time	$V_{dd} = -9.5V$, $I_F = -1A$, di/dt = 200A/µs		23		ns

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ ⁽²⁾			200	°C/W
	JA Thermal Resistance Junction to Ambient ^{(3) (2)}			94	°C/W

(1) Device mounted on FR4 material with Minimum Cu mounting area.

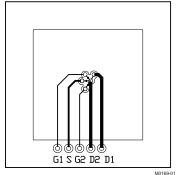
(2) Measured with both devices biased in a parallel condition.

(3) Device mounted on FR4 material with $1-inch^2$ of Cu (2oz).

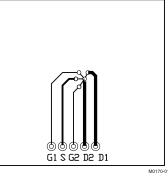


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 $\begin{array}{l} Max \; R_{\theta JA} = 94^{\circ}C/W \\ when mounted on \\ 1 \; inch^2 \; (6.45 \; cm^2) \; of \\ 2 \hbox{-}oz. \; (0.071 \hbox{-}mm \; thick) \\ Cu. \end{array}$



Max $R_{\theta,JA} = 200^{\circ}C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

Graphs are Per MOSFET at $T_A = 25^{\circ}$ C, unless stated otherwise. Drain to Drain measurements are done with both MOSFETs in series (common source configuration).

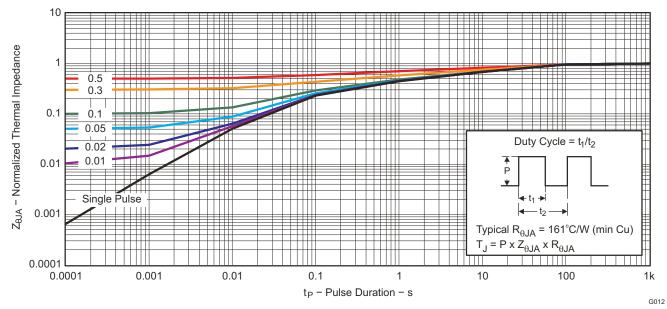
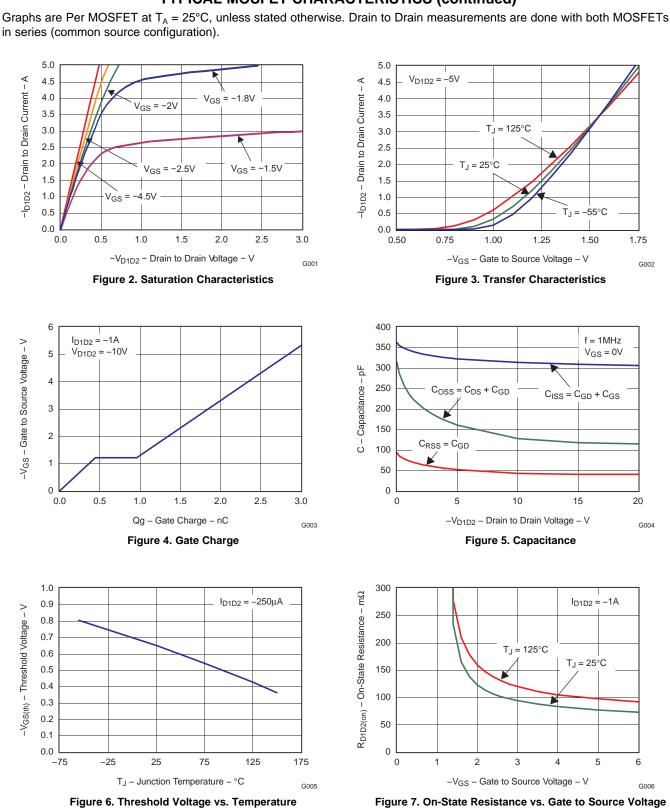


Figure 1. Transient Thermal Impedance

TEXAS INSTRUMENTS

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4



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TYPICAL MOSFET CHARACTERISTICS (continued)

Graphs are Per MOSFET at $T_A = 25^{\circ}$ C, unless stated otherwise. Drain to Drain measurements are done with both MOSFETs in series (common source configuration).

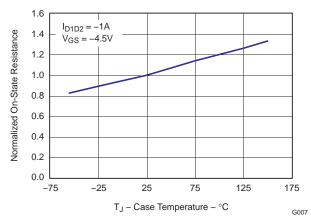


Figure 8. Normalized On-State Resistance vs. Temperature

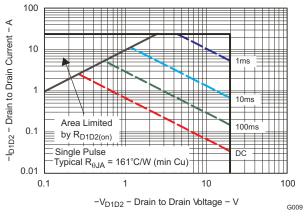


Figure 10. Maximum Safe Operating Area

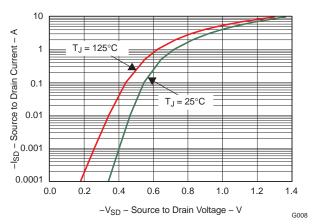


Figure 9. Typical Diode Forward Voltage

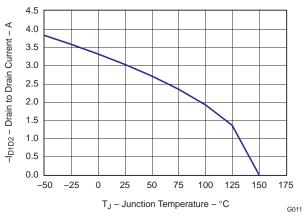


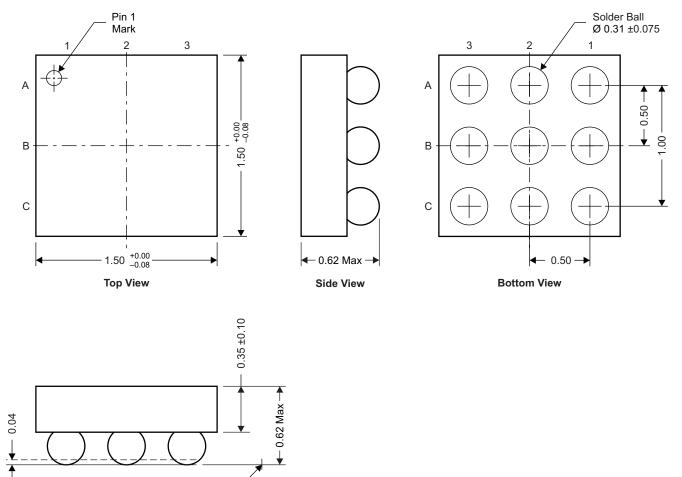
Figure 11. Maximum Drain Current vs. Temperature



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MECHANICAL DATA

CSD75204W15 Package Dimensions



Front View

M0171-01

NOTE: All dimensions are in mm (unless otherwise specified)

Seating Plate

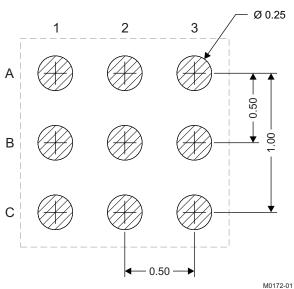
Pinout

POSITION	DESIGNATION
A1	Gate1
A2, A3, B3	Drain1
C1	Gate2
C2, C3, B2	Drain2
B1	Source Sense



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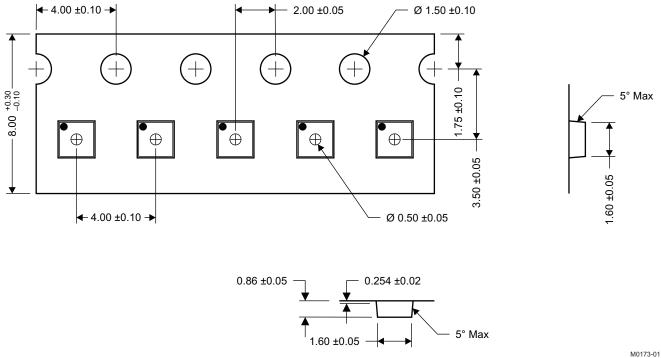
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Land Pattern Recommendation

NOTE: All dimensions are in mm (unless otherwise specified)





NOTE: All dimensions are in mm (unless otherwise specified)

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8

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C	Changes from Original (October 2009) to Revision A		
•	Deleted the Package Marking Information sectiom	7	

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